

Ge Substrate Wafers

Monocrystalline Ge wafer is important semiconductor substrate materials. It's mainly used for substrate materials to Concentrator Photovoltaic power station (CPV), Space solar cell panels and ultra-high brightness LED. We provide Low EPD or Zero EPD Ge substrate which diameter includes 2", 3", 4" and 6". Custom-made Ge substrate is available upon request.

Item	Unit	Semiconduct Specifications	
Crystal Growth Method		CZ	
Conduct Type		(n-type)	(p-type)
Dopant		As,Sb	Ga
Diameter	inch	2", 3", 4" and 6"	
Wafer Orientation*		(100)±0.5°	
OF/IF		US,EJ	
Laser Marking		Upon request	
Thickness*	μm	(175-500)±25	
Resistivity(at RT)	ohm.cm	0.005-30	0.005-0.04
Etch Pit Density (EPD)	/cm ²	≤300	≤300
TTV	μm	≤15	≤15
Warp	μm	≤25	≤25
Backside Ra	μm	<0.1	<0.1
Surface	Side1/ Side2	E/E, P/E, P/D	
Epi-ready		Yes	
Package		Cassette or single wafer container	

* Wafer Orientation and Thickness are available upon request

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